

#### ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises an insulating film 114 formed mainly of a film of polyallyl ether resin; an interconnection structure 116 buried in the insulating film 114, and having a via portion buried in a groove-shaped via hole and an interconnection portion formed on the via portion and having an eave-shaped portion horizontally extended beyond the via portion; an insulating film 118 formed on the insulating film 114 with the interconnection structure 116 buried in and formed mainly of a film of organosilicate glass; and an interconnection structure 120 buried in the insulating film 118 and connected to the interconnection structure 116. Thus, the stresses to be exerted to the insulating films are decreased, the generation of cracks and peelings generated in the interfaces between the insulating films and in the insulating films due to the stresses generated at the ends of the interconnection structures can be effectively prevented.